PNP Epitaxial Silicon Transistor

KSA916

Features

- Audio Power Amplifier
- Driver Stage Amplifier
- Complement to KSC2316

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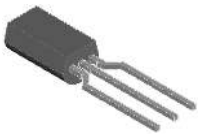


TO−92 3 LF
CASE 135AM

ABSOLUTE MAXIMUM RATINGS

(Values are at T_A = 25°C unless otherwise noted.)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector−Base Voltage	−120	V
V_{CEO}	Collector−Emitter Voltage	−120	V
V_{EBO}	Emitter−Base Voltage	−5	V
I_C	Collector Current	−800	mA
T_J	Junction Temperature	150	°C
T_{STG}	Storage Temperature	−55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

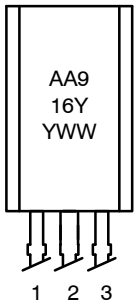
THERMAL CHARACTERISTICS

(Values are at T_A = 25°C unless otherwise noted.) (Note 1)

Symbol	Parameter	Value	Unit
P_D	Power Dissipation, by $R_{\theta JA}$	900	mW
	Power Dissipation, by $R_{\theta JC}$	3	W
	Derate Above 25°C, by $R_{\theta JA}$	7.2	mW/°C
	Derate Above 25°C, by $R_{\theta JC}$	24	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction−to−Ambient	130	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction−to−Case	41	°C/W

1. PCB size: FR−4, 76 mm × 114 mm × 1.57 mm (3.0 inch × 4.5 inch × 0.062 inch) with minimum land pattern size.

MARKING DIAGRAM



1: Emitter
2: Collector
3: Base

A = Assembly Code
A916Y = Device Code
YWW = Date Code

ORDERING INFORMATION

Device	Package	Shipping
KSA916YTA	TO−92 3 LF (Pb−Free)	2000 / Fan−Fold

ELECTRICAL CHARACTERISTICS

(Values are at T_A = 25°C unless otherwise noted.)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{CBO}	Collector−Base Breakdown Voltage	I_C = −1 mA, I_E = 0	−120	–	–	V
BV_{CEO}	Collector−Emitter Breakdown Voltage	I_C = −10 mA, I_B = 0	−120	–	–	V
BV_{EBO}	Emitter−Base Breakdown Voltage	I_E = −1 mA, I_C = 0	−5	–	–	V
I_{CBO}	Collector Cut−Off Current	V_{CB} = −120 V, I_E = 0	–	–	−0.1	μA
h_{FE1}	DC Current Gain	V_{CE} = −5 V, I_C = −10 mA	60	–	–	
h_{FE2}	DC Current Gain	V_{CE} = −5 V, I_C = −100 mA	80	–	240	
V_{CE}(sat)	Collector−Emitter Saturation Voltage	I_C = −500 mA, I_B = −50 mA	–	–	−1	V
f_T	Current Gain Bandwidth Product	V_{CE} = −5 V, I_C = −100 mA	–	120	–	MHz
C_{ob}	Output Capacitance	V_{CB} = −10 V, I_E = 0, f = 1 MHz	–	–	40	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

h_{FE} CLASSIFICATION

Classification	O	Y
h_{FE2}	80 ~ 160	120 ~ 240

TYPICAL PERFORMANCE CHARACTERISTICS

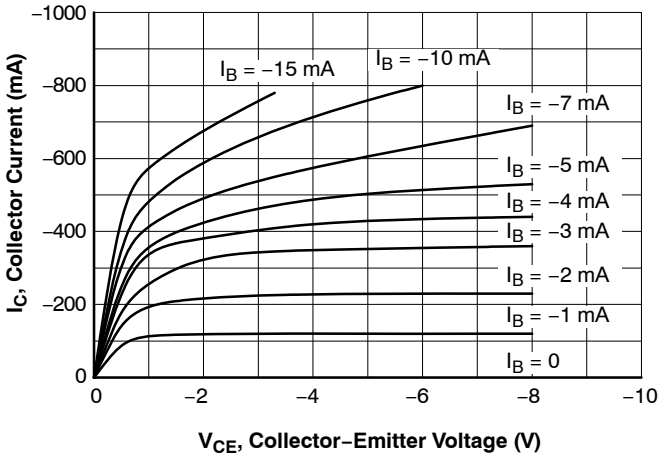


Figure 1. Static Characteristic

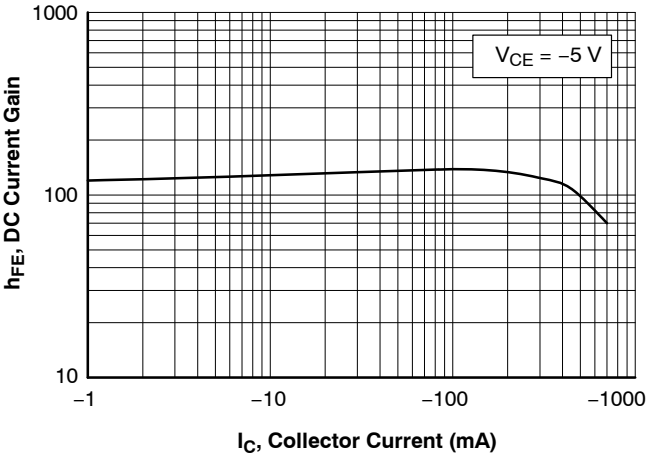


Figure 2. DC Current Gain

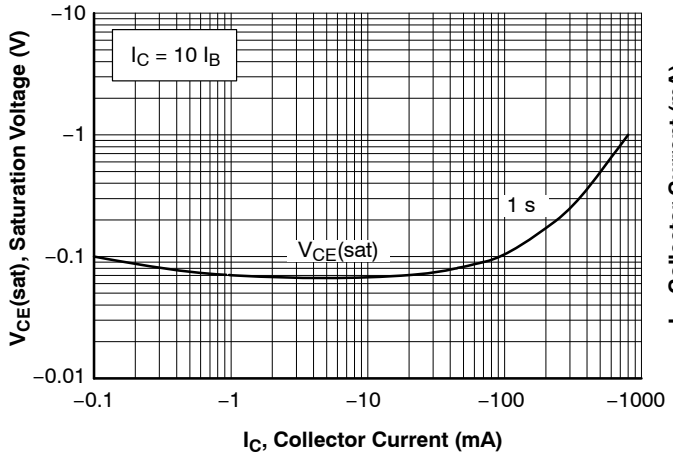


Figure 3. Collector−Emitter Saturation Voltage

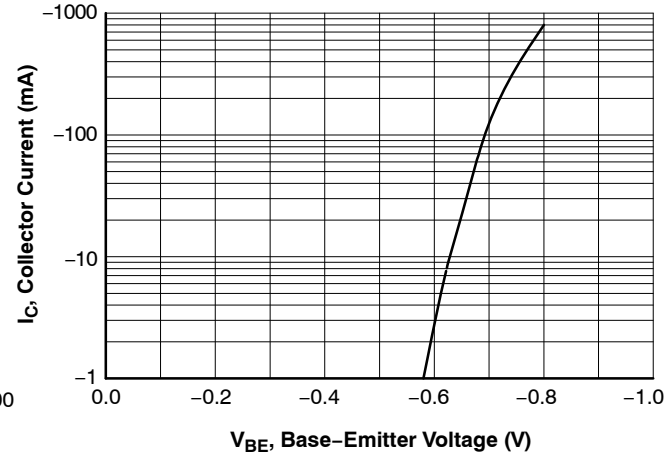


Figure 4. Base−Emitter On Voltage

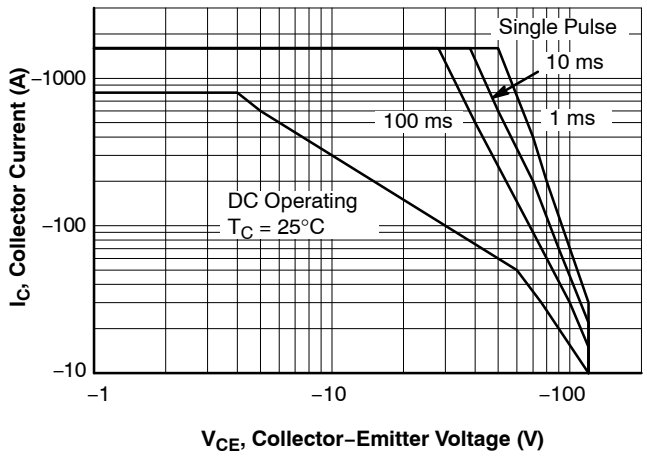


Figure 5. Safe Operating Area

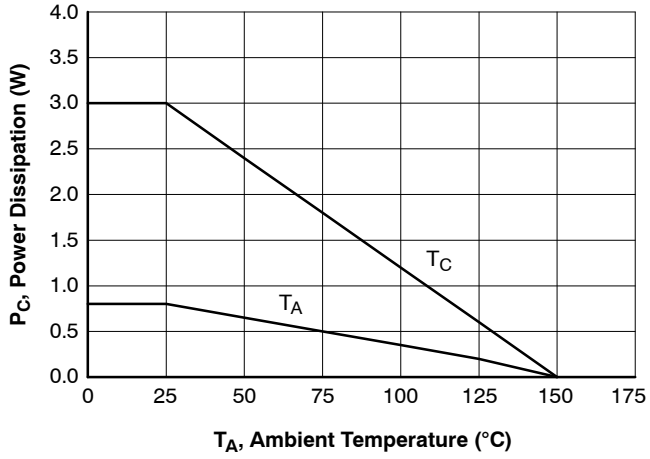
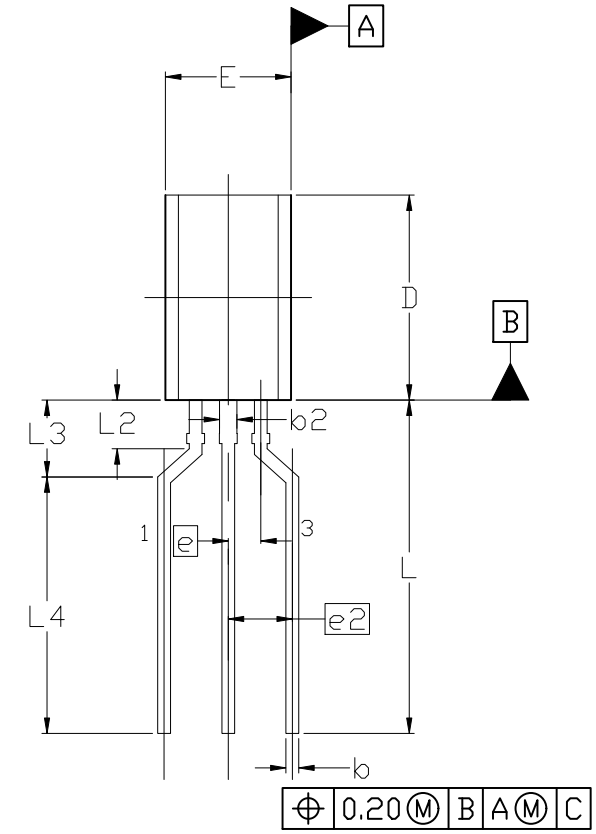


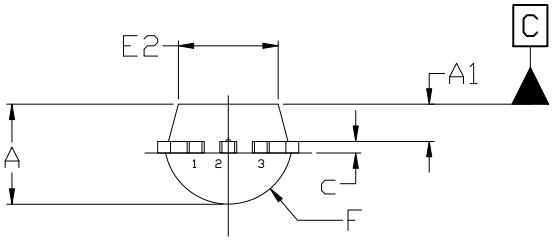
Figure 6. Power Derating

TO−92 3 8.0x4.9 (LEADFORMED)
CASE 135AM
ISSUE B

DATE 14 JAN 2021



TOP VIEW



END VIEW

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, GATE REMAINS AND TIE BAR PROTRUSIONS.
4. DIMENSION b AND b2 DOES NOT INCLUDE DAMBAR PROTRUSION. DIMENSION b2 LOCATED ABOVE THE DAMBAR PORTION OF MIDDLE LEAD.

	MILLIMETERS		
DIM	MIN.	NOM.	MAX.
A	3.70	3.90	4.10
A1	1.25	1.45	1.65
b	0.35	0.50	0.60
b2	0.62	---	0.78
c	0.35	0.45	0.55
D	7.80	8.00	8.20
E	4.70	4.90	5.10
E2	3.70	3.90	4.10
e	1.27 BSC		
e2	2.50 BSC		
F	2.45 REF		
L	13.00 REF		
L2	1.50	---	1.90
L3	2.60	---	3.40
L4	10.40 REF		

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